

In the claims:

1. (Canceled) .
2. (Canceled) .
3. (Canceled) .
4. (Canceled) .
5. (Canceled) .
6. (Canceled) .
7. (Canceled) .
8. (Canceled) .
9. (Canceled) .
10. (Canceled) .
11. (Canceled) .
12. (Canceled) .
13. (Canceled) .
14. (Canceled) .
15. (Canceled) .

16. (Canceled).

17. (Canceled).

18. (Canceled).

19. (Canceled).

20. (Canceled).

21. (Canceled).

22. (Canceled).

23. (Canceled).

24. (New) A method of protecting a semiconductor device from damage during device processing comprising:

providing a semiconductor wafer;

providing a plurality of active semiconductor devices on the surface of the wafer wherein each active device is separated from other active devices by inactive semiconductor areas not including an active semiconductor device;

providing a plurality of metallic pads around the periphery of an active device only in said inactive areas on the surface of the wafer, each pad having a greater relative height measured from the surface of the wafer than the height of any portion of a respective active device;

dicing the wafer into a plurality of die; and

removing a die from the wafer using a pick and place tool such that the pick and place tool only makes contact

with the pads surrounding the active devices of the wafer thereby reducing the likelihood of contact with the active device.

25. (New) The method of protecting the semiconductor device as in claim 24 wherein the active device further comprises a ridge waveguide laser.

26. (New) The method of protecting the semiconductor device as in claim 24 wherein the plurality of pads further comprises three pads.

27. (New) The method of protecting the semiconductor device as in claim 24 further comprising using the plurality of metallic pads as reticles.

28. (New) A method of protecting a semiconductor device from damage during device processing comprising:

providing a semiconductor wafer;

providing a plurality of semiconductor chips on the surface of the wafer where each semiconductor chip includes an active area bounded by inactive semiconductor areas not including an active semiconductor device;

providing a plurality of pads around the periphery of at least some semiconductor chips of the plurality of semiconductor chips only in said inactive areas on the surface of the at least some semiconductor chips, each pad having a greater relative height measured from the surface of the wafer than the height of any portion of a respective active device; and

removing a semiconductor chip of the at least some semiconductor chips from the wafer using a pick and place

tool such that the pick and place tool only makes contact with the pads surrounding the active area of the semiconductor chip thereby reducing the likelihood of contact with the active area.

29. (New) The method of protecting the semiconductor device as in claim 28 wherein the active device further comprises a ridge waveguide laser.

30. (New) The method of protecting the semiconductor device as in claim 28 wherein the plurality of pads further comprises three pads.

31. (New) The method of protecting the semiconductor device as in claim 28 further comprising using the plurality of metallic pads as reticles.

32. (New) The method of protecting the semiconductor device as in claim 28 wherein the plurality of pads further comprise metallic pads.

33. (New) The method of protecting the semiconductor device as in claim 28 wherein the plurality of pads further comprise non-metallic pads.

34. (New) The method of protecting the semiconductor device as in claim 28 wherein the non-metallic pads further comprise dielectric pads.

35. (New) A method of protecting a semiconductor device from damage during device processing comprising:
providing a semiconductor wafer;

providing a semiconductor chip on the surface of the wafer where the semiconductor chip includes an active area with inactive semiconductor areas disposed on opposing sides of the active area and where the inactive semiconductor areas do not include an active semiconductor device;

providing a plurality of pads only in said inactive areas on the surface of the semiconductor chip, each pad having a greater relative height measured from the surface of the wafer than the height of any portion of a respective active device; and

removing the semiconductor chip from the wafer using a pick and place tool such that the pick and place tool only makes contact with the pads surrounding the active area of the semiconductor chip thereby reducing the likelihood of contact with the active area.

36. (New) The method of protecting the semiconductor device as in claim 35 wherein the active device further comprises a ridge waveguide laser.

37. (New) The method of protecting the semiconductor device as in claim 35 wherein the plurality of pads further comprises three pads.

38. (New) The method of protecting the semiconductor device as in claim 35 further comprising using the plurality of metallic pads as reticles.

39. (New) The method of protecting the semiconductor device as in claim 35 wherein the plurality of pads further comprise metallic pads.

40. (New) The method of protecting the semiconductor device as in claim 35 wherein the plurality of pads further comprise non-metallic pads.

41. (New) The method of protecting the semiconductor device as in claim 35 wherein the non-metallic pads further comprise dielectric pads.

42. (New) A semiconductor comprising:

a plurality of active semiconductor devices disposed on the surface of the wafer wherein each active device is separated from other active devices by inactive semiconductor areas not including an active semiconductor device; and

a plurality of metallic pads disposed around the periphery of an active device only in said inactive areas on the surface of the wafer, each pad having a greater relative height measured from the surface of the wafer than the height of any portion of a respective active device and adapted for engaging respective contacts on an external pick and place tool that removes a die from the wafer, the greater relative height of the plurality of pads causing the pick and place tool to only make contact with the pads surrounding the active devices of the wafer thereby reducing the likelihood of contact with the active device.